

### **Features**

- Trench Power LV MOSFET Technology
- High Density Cell Design for Low R<sub>DS(ON)</sub>
- · High Speed Switching
- Moisture Sensitivity Level 1
- Halogen Free. "Green" Device (Note 1)
- · Epoxy Meets UL 94 V-0 Flammability Rating
- Lead Free Finish/RoHS Compliant ("P" Suffix Designates RoHS Compliant. See Ordering Information)

## **Maximum Ratings**

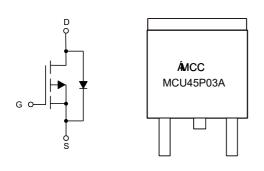
- Operating Junction Temperature Range : -55°C to +150°C
- Storage Temperature Range: -55°C to +150°C
- Thermal Resistance: 2°C/W Junction to Case

Parameter		Symbol	Rating	Unit	
Drain-Source Voltage		V <sub>DS</sub>	-30	V	
Gate-Source Volltage		V <sub>GS</sub>	±25	V	
Continuous Drain Current	T <sub>C</sub> =25°C		-45	Α	
	T <sub>C</sub> =85°C	⊢ I <sub>D</sub>	-32		
Pulsed Drain Current <sup>(2)</sup>		I <sub>DM</sub>	-175	Α	
Total Power Dissipation		P <sub>D</sub>	62.5	W	
Single Pulsed Avalanche Energy		E <sub>AS</sub>	145	mJ	

#### Note:

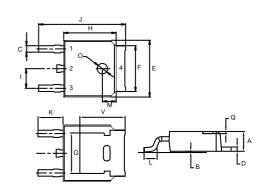
- 1.Halogen free "Green" products are defined as those which contain <900ppm bromine,<900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 2. Pulse Test: Pulse Width≤300µs,Duty Cycle ≤2%.

# **Internal Structure and Marking Code**



# P-CHANNEL MOSFET

# **DPAK(TO-252)**



- 1. Gate
- 2,4. Drain
  - 3. Source

DIMENSIONS					
DIM INCH		HES	ES MM		NOTE
DIIVI	MIN	MAX	MIN	MAX	NOTE
Α	0.087	0.094	2.20	2.40	
В	0.000	0.005	0.00	0.13	
С	0.026	0.034	0.66	0.86	
D	0.018	0.023	0.46	0.58	
Е	0.256	0.264	6.50	6.70	
F	0.201	0.215	5.10	5.46	
G	0.190		4.83		TYP.
Н	0.236	0.244	6.00	6.20	
ı	0.086	0.094	2.18	2.39	
J	0.386	0.409	9.80	10.40	
K	0.114		2.90		TYP.
L	0.055	0.067	1.40	1.70	
M	0.063		1.60		TYP.
0	0.043	0.051	1.10	1.30	
Q	0.000	0.012	0.00	0.30	
V	0.211		5.35		TYP.

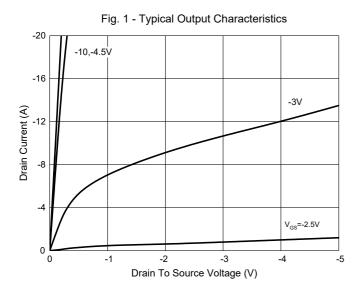


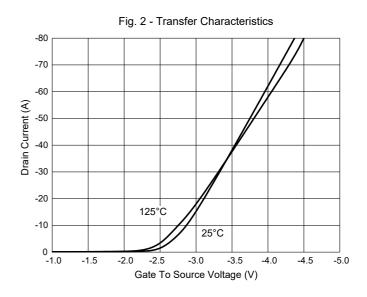
# Electrical Characteristics @ 25°C (Unless Otherwise Specified)

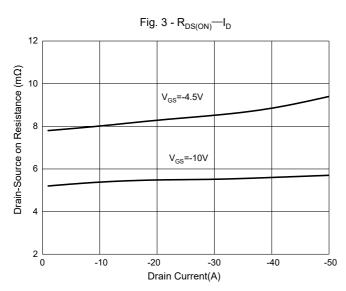
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static Characteristics				1		I	
Drain-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250μA	-30			V	
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> =0V, V <sub>GS</sub> =±25V			±100	nA	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μA	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-1.2	-1.8	-2.8	V	
		V <sub>GS</sub> =-20V, I <sub>D</sub> =-20A		4.8	7	8	
Drain Caura On Basistanas	Ь	V <sub>GS</sub> =-10V, I <sub>D</sub> =-15A		5.5	8		
Drain-Source On-Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-6V, I <sub>D</sub> =-12A	$I_{GS}$ =-6V, $I_{D}$ =-12A 6.5		12	mΩ	
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-12A		8	13	1	
Diode Characteristics							
Continuous Body Diode Current	Is				-45	Α	
Diode Forward Voltage	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-20A			-1.2	V	
Reverse Recovery Time	t <sub>rr</sub>	I <sub>S</sub> =-20A, dI <sub>F</sub> /dt=100A/μs		18		ns	
Reverse Recovery Charge	Q <sub>rr</sub>	- 1 <sub>S</sub> 20A, αι <sub>F</sub> /αι-100A/μS		7.8		nC	
Dynamic Characteristics							
Input Capacitance	C <sub>iss</sub>			2152			
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-15V,V <sub>GS</sub> =0V,f=1MHz		308		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			242			
Total Gate Charge	$Q_g$			40			
Gate-Source Charge	$Q_{gs}$	V <sub>DS</sub> =-15V,V <sub>GS</sub> =10V,I <sub>D</sub> =-12A		8.4		nC	
Gate-Drain Charge	$Q_{gd}$			8.6			
Turn-On Delay Time	t <sub>d(on)</sub>			8			
Turn-On Rise Time	t <sub>r</sub>	V <sub>DD</sub> =-15V, V <sub>GS</sub> =-10V,		19			
Turn-Off Delay Time	t <sub>d(off)</sub>	$R_{GEN}$ =2.5 $\Omega$ , $I_D$ =-1A		75		ns	
Turn-Off Fall Time	t <sub>f</sub>			46			

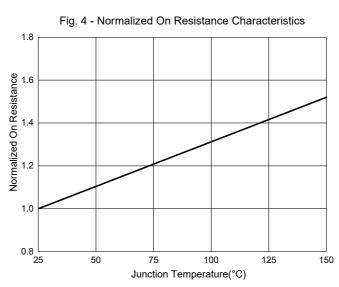


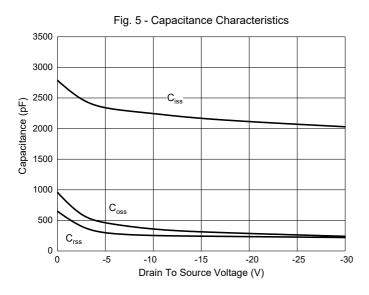
### **Curve Characteristics**

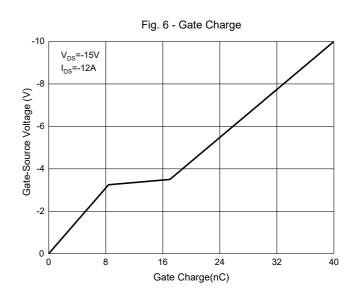






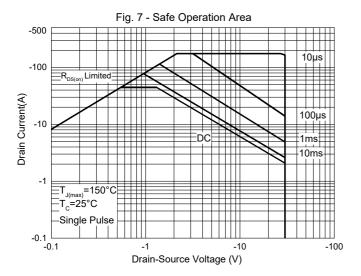








## **Curve Characteristics**





## **Ordering Information**

Device	Packing
Part Number-TP	Tape&Reel: 2.5Kpcs/Reel

#### \*\*\*IMPORTANT NOTICE\*\*\*

**Micro Commercial Components Corp.** reserves the right to make changes without further notice to any product herein to make corrections, modifications, enhancements, improvements, or other changes. **Micro Commercial Components Corp**. does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold **Micro Commercial Components Corp**, and all the companies whose products are represented on our website, harmless against all damages. **Micro Commercial Components Corp**, products are sold subject to the general terms and conditions of commercial sale, as published at

https://www.mccsemi.com/Home/TermsAndConditions.

#### \*\*\*LIFE SUPPORT\*\*\*

MCC's products are not authorized for use as critical components in life support devices or systems without the express written approval of Micro Commercial Components Corporation.

#### \*\*\*CUSTOMER AWARENESS\*\*\*

Counterfeiting of semiconductor parts is a growing problem in the industry. Micro Commercial Components (MCC) is taking strong measures to protect ourselves and our customers from the proliferation of counterfeit parts. MCC strongly encourages customers to purchase MCC parts either directly from MCC or from Authorized MCC Distributors who are listed by country on our web page cited below. Products customers buy either from MCC directly or from Authorized MCC Distributors are genuine parts, have full traceability, meet MCC's quality standards for handling and storage. MCC will not provide any warranty coverage or other assistance for parts bought from Unauthorized Sources. MCC is committed to combat this global problem and encourage our customers to do their part in stopping this practice by buying direct or from authorized distributors.